

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-3.8	A
		T <sub>A</sub> = +70°C		-2.9	
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	-11	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	R <sub>θJA</sub>	115	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-800	nA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	-1.8	-2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	56	70	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A
			98	120		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	3.6	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.7A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	—	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.7A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	336	1008	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	70	210	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	49	147	pF	
Gate Resistance	R <sub>G</sub>	—	4.6	—	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz
<b>SWITCHING CHARACTERISTICS (Note 9)</b>						
Total Gate Charge	Q <sub>g</sub>	—	4.0	8.0	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.8A
		—	7.8	—		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A
Gate-Source Charge	Q <sub>gs</sub>	—	1.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.5	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A, R <sub>G</sub> = 6.0Ω
Turn-On Delay Time	t <sub>d(on)</sub>	—	6.0	12.0		
Rise Time	t <sub>r</sub>	—	5.0	10.0		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	17.6	35.2		
Fall Time	t <sub>f</sub>	—	9.5	19.0		

- Notes:
6. Device mounted on FR-4 PCB on 2 oz., 0.5 in.<sup>2</sup> copper pads and t ≤ 5 sec.
  7. Pulse width ≤ 10μs, Duty Cycle ≤ 1%.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.

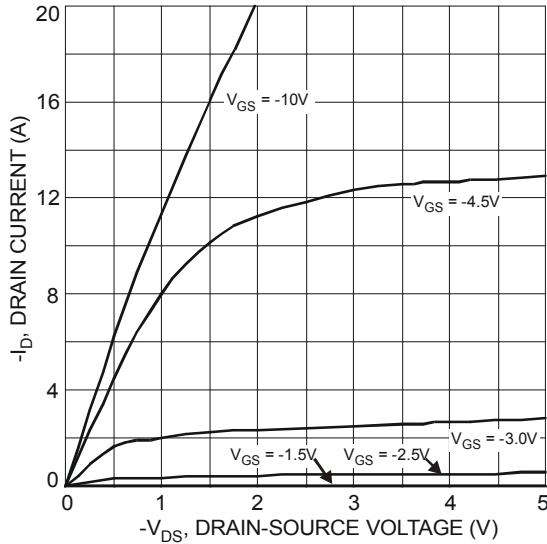


Fig. 1 Typical Output Characteristics

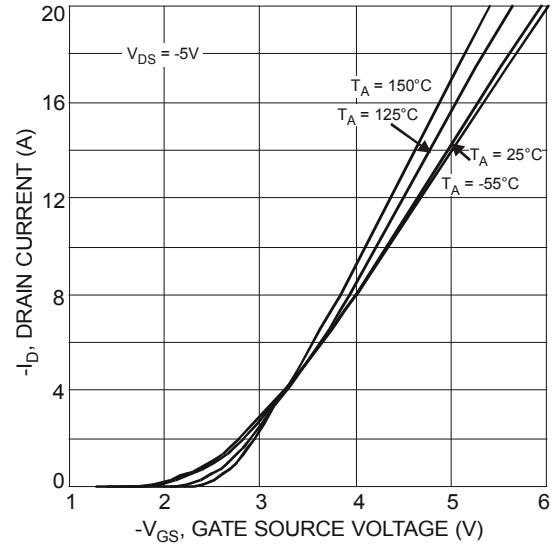


Fig. 2 Typical Transfer Characteristics

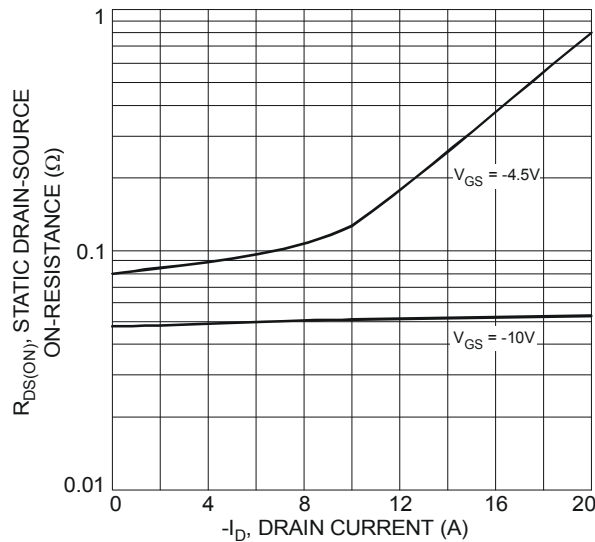


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

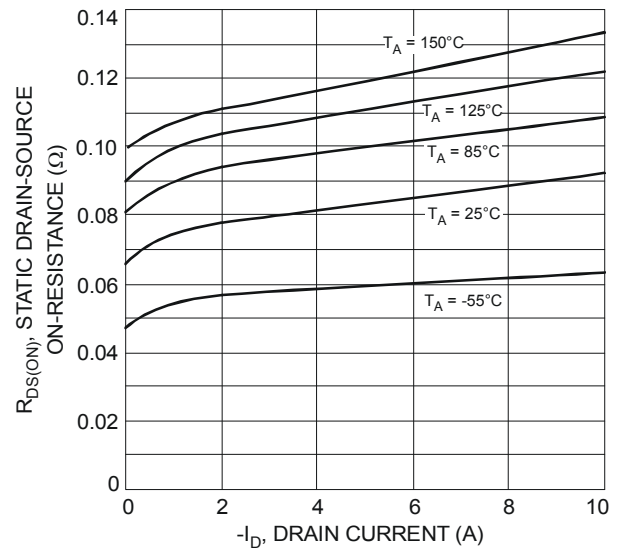


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

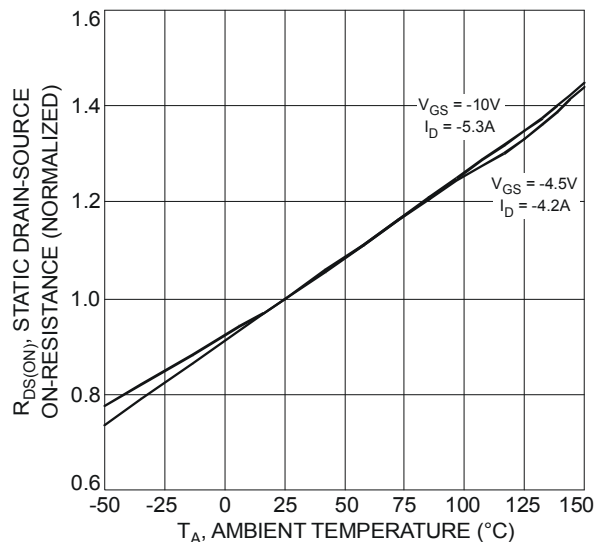


Fig. 5 On-Resistance Variation with Temperature

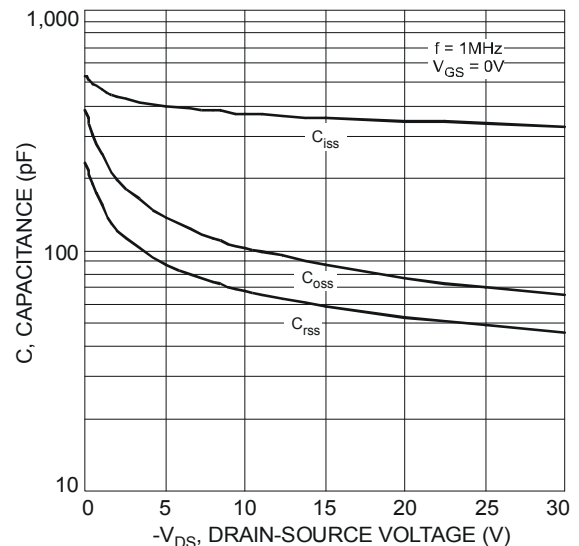


Fig. 6 Typical Capacitance

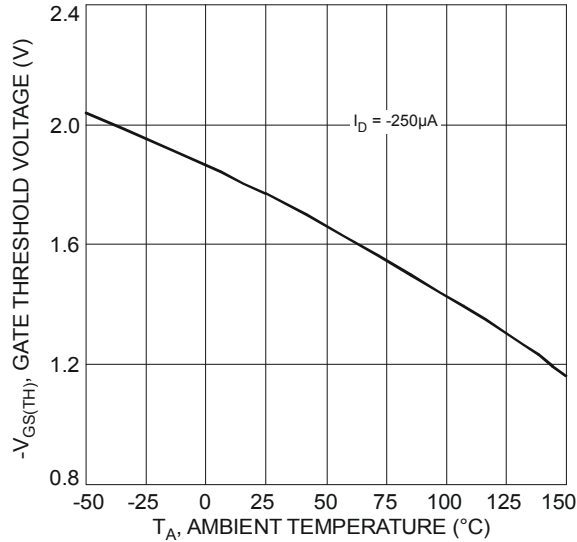


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

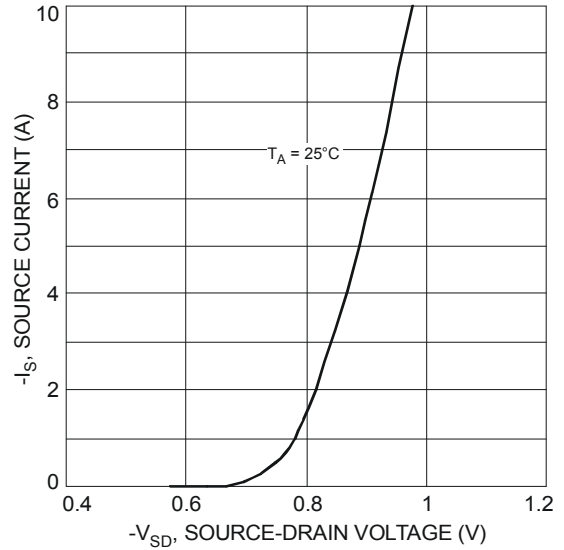


Fig. 8 Diode Forward Voltage vs. Current

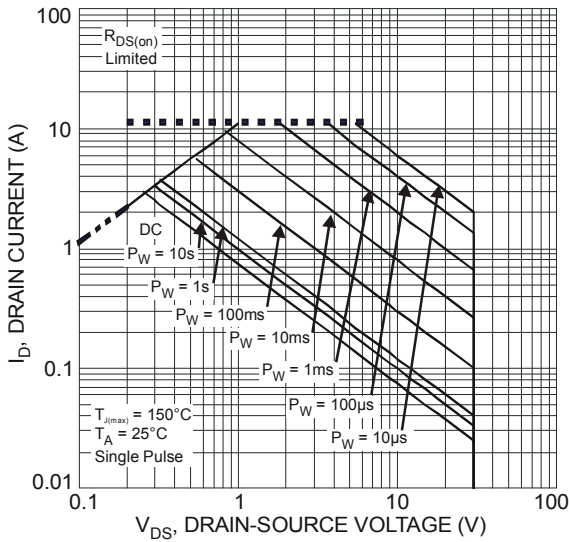
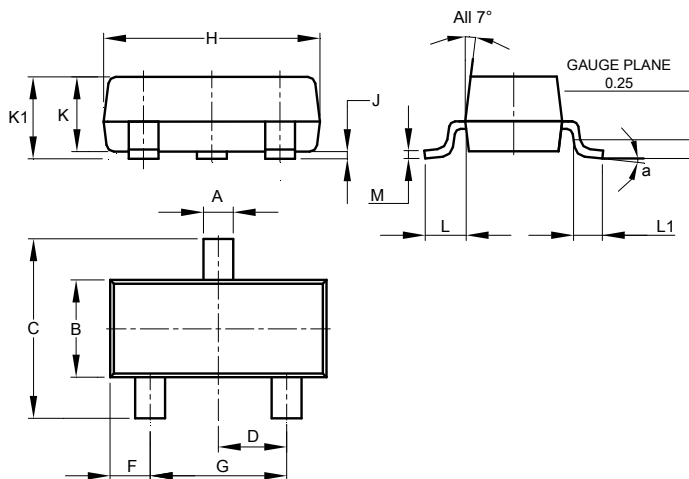


Fig. 9 Safe Operation Area

## Package Outline Dimensions

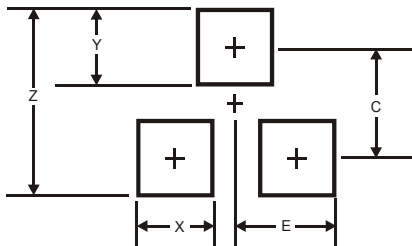
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
$\alpha$	8°		
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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